

- **Member of the Texas Instruments Widebus™ Family**
- **EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Plastic 300-mil Thin Shrink Small-Outline Package**

### description

This 1-bit-to-2-bit address driver is designed for 2.3-V to 3.6-V  $V_{CC}$  operation.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVCH162830 is packaged in TI's thin shrink small-outline (DBB) package, which provides twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH162830 is characterized for operation from -40°C to 85°C.

**FUNCTION TABLE**

INPUTS			OUTPUTS	
$\overline{OE1}$	$\overline{OE2}$	A	1Yn	2Yn
L	H	H	H	Z
L	H	L	L	Z
H	L	H	Z	H
H	L	L	Z	L
L	L	H	H	H
L	L	L	L	L
H	H	X	Z	Z

**DBB PACKAGE**  
(TOP VIEW)

2Y2	1	80	1Y3
1Y2	2	79	2Y3
GND	3	78	GND
2Y1	4	77	1Y4
1Y1	5	76	2Y4
$V_{CC}$	6	75	$V_{CC}$
A1	7	74	1Y5
A2	8	73	2Y5
GND	9	72	GND
A3	10	71	1Y6
A4	11	70	2Y6
GND	12	69	GND
A5	13	68	1Y7
A6	14	67	2Y7
$V_{CC}$	15	66	$V_{CC}$
A7	16	65	1Y8
A8	17	64	2Y8
GND	18	63	GND
A9	19	62	1Y9
$\overline{OE1}$	20	61	2Y9
$\overline{OE2}$	21	60	1Y10
A10	22	59	2Y10
GND	23	58	GND
A11	24	57	1Y11
A12	25	56	2Y11
$V_{CC}$	26	55	$V_{CC}$
A13	27	54	1Y12
A14	28	53	2Y12
GND	29	52	GND
A15	30	51	1Y13
A16	31	50	2Y13
GND	32	49	GND
A17	33	48	1Y14
A18	34	47	2Y14
$V_{CC}$	35	46	$V_{CC}$
2Y18	36	45	1Y15
1Y18	37	44	2Y15
GND	38	43	GND
2Y17	39	42	1Y16
1Y17	40	41	2Y16



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

PRODUCT PREVIEW information concerns products in the formative or design phase of development. Characteristic data and other specifications are design goals. Texas Instruments reserves the right to change or discontinue these products without notice.

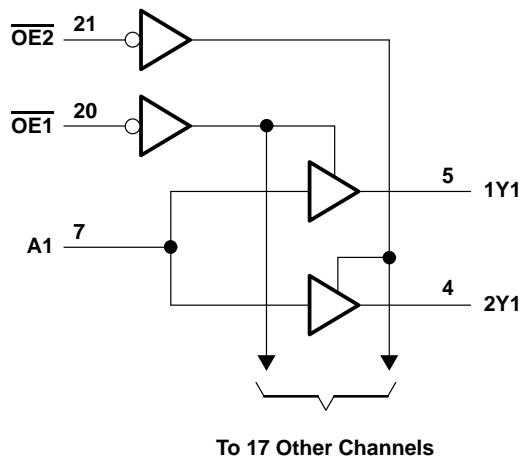


POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1996, Texas Instruments Incorporated

**PRODUCT PREVIEW**

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, $V_{CC}$	–0.5 V to 4.6 V
Input voltage range, $V_I$ (see Note 1)	–0.5 V to 4.6 V
Output voltage range, $V_O$ (see Notes 1 and 2)	–0.5 V to $V_{CC} + 0.5$ V
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	–50 mA
Output clamp current, $I_{OK}$ ( $V_O < 0$ or $V_O > V_{CC}$ )	±50 mA
Continuous output current, $I_O$ ( $V_O = 0$ to $V_{CC}$ )	±50 mA
Continuous current through each $V_{CC}$ or GND	±100 mA
Maximum power dissipation at $T_A = 55^{\circ}\text{C}$ (in still air) (see Note 3)	0.84 W
Storage temperature range, $T_{stg}$	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
  2. This value is limited to 4.6 V maximum.
  3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the *ABT Advanced BiCMOS Technology Data Book*.

**recommended operating conditions (see Note 4)**

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2.3	3.6	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2		
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V		0.8	
V <sub>I</sub>	Input voltage		0	V <sub>CC</sub>	V
V <sub>O</sub>	Output voltage		0	V <sub>CC</sub>	V
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 2.3 V		–6	mA
		V <sub>CC</sub> = 2.7 V		–8	
		V <sub>CC</sub> = 3 V		–12	
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 2.3 V		6	mA
		V <sub>CC</sub> = 2.7 V		8	
		V <sub>CC</sub> = 3 V		12	
Δt/Δv	Input transition rise or fall rate		0	10	ns/V
T <sub>A</sub>	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

**PRODUCT PREVIEW**

**SN74ALVCH162830**  
**1-TO-2 ADDRESS DRIVER**  
**WITH 3-STATE OUTPUTS**

SCES082 – AUGUST 1996

**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> <sup>†</sup>	MIN	TYP <sup>‡</sup>	MAX	UNIT
V <sub>OH</sub>	I <sub>OH</sub> = −100 μA		MIN to MAX	V <sub>CC</sub> −0.2			V
	I <sub>OH</sub> = −4 mA, V <sub>IH</sub> = 1.7 V		2.3 V	1.9			
	I <sub>OH</sub> = −6 mA	V <sub>IH</sub> = 1.7 V	2.3 V	1.7			
		V <sub>IH</sub> = 2 V	3 V	2.4			
	I <sub>OH</sub> = −8 mA, V <sub>IH</sub> = 2 V		2.7 V	2			
	I <sub>OH</sub> = −12 mA, V <sub>IH</sub> = 2 V		3 V	2			
V <sub>OL</sub>	I <sub>OL</sub> = 100 μA		MIN to MAX			0.2	V
	I <sub>OL</sub> = 4 mA, V <sub>IL</sub> = 0.7 V		2.3 V			0.4	
	I <sub>OL</sub> = 6 mA	V <sub>IL</sub> = 0.7 V	2.3 V			0.55	
		V <sub>IL</sub> = 0.8 V	3 V			0.55	
	I <sub>OL</sub> = 8 mA, V <sub>IL</sub> = 0.8 V		2.7 V			0.6	
	I <sub>OL</sub> = 12 mA, V <sub>IL</sub> = 0.8 V		3 V			0.8	
I <sub>I</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND		3.6 V			±5	μA
I <sub>I</sub> (hold)	V <sub>I</sub> = 0.7 V		2.3 V	45			μA
	V <sub>I</sub> = 1.7 V			−45			
	V <sub>I</sub> = 0.8 V		3 V	75			
	V <sub>I</sub> = 2 V			−75			
	V <sub>I</sub> = 0 to 3.6 V <sup>§</sup>		3.6 V			±500	
I <sub>OZ</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND		3.6 V			±10	μA
I <sub>CC</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0		3.6 V			40	μA
ΔI <sub>CC</sub>		One input at V <sub>CC</sub> − 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 3.6 V			750	μA
C <sub>i</sub>	Control inputs	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V				pF
	Data inputs						
C <sub>O</sub>	Outputs	V <sub>O</sub> = V <sub>CC</sub> or GND	3.3 V				pF

$^{\dagger}$  For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

$^{\ddagger}$  All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

$^{\S}$  This is the bus-hold maximum dynamic current required to switch the input from one state to another.

**switching characteristics over recommended operating free-air temperature range,  $C_L = 50 \text{ pF}$  (unless otherwise noted) (see Figures 1 and 2)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$		$V_{CC} = 2.7 \text{ V}$		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
$t_{pd}$	A	Y							ns
$t_{en}$	$\overline{OE}$	Y							ns
$t_{dis}$	$\overline{OE}$	Y							ns

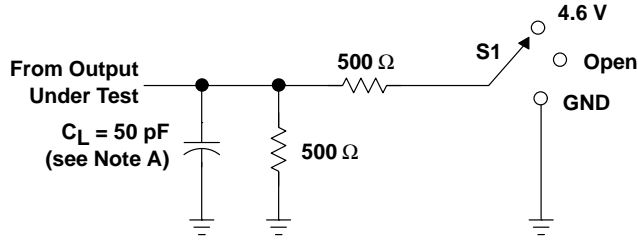
**operating characteristics,  $T_A = 25^{\circ}\text{C}$**

PARAMETER		TEST CONDITIONS	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	UNIT
			TYP	TYP	
$C_{pd}$	Power dissipation capacitance	Outputs enabled	$C_L = 0 \text{ pF}, f = 10 \text{ MHz}$		pF
		Outputs disabled			



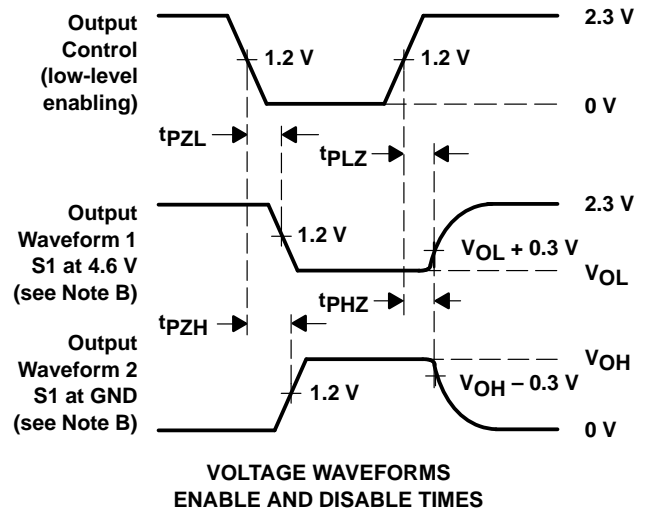
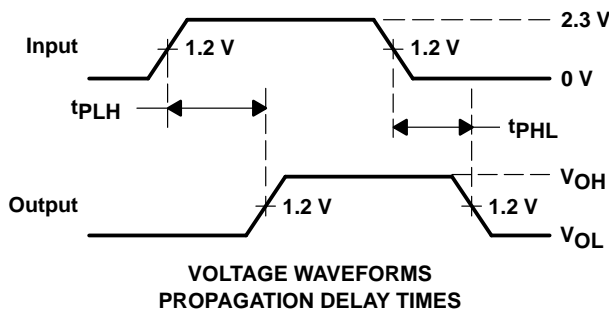
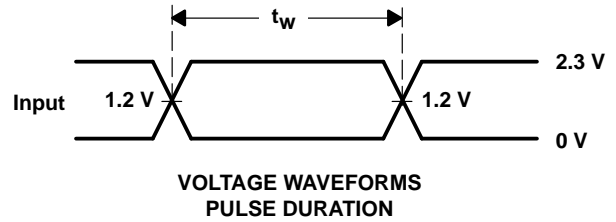
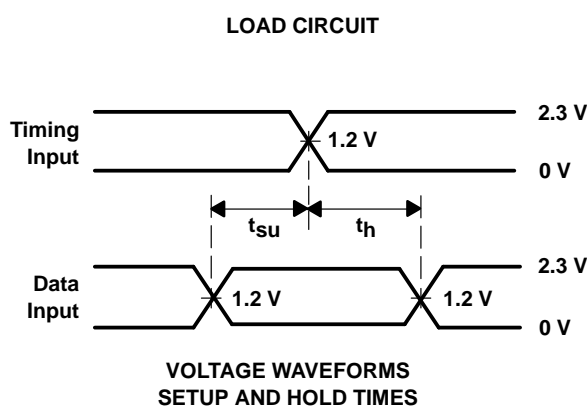
# PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$$



LOAD CIRCUIT

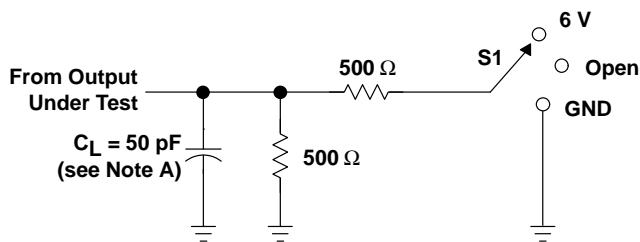
TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	4.6 V
$t_{PHZ}/t_{PZH}$	GND



- NOTES:
- $C_L$  includes probe and jig capacitance.
  - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - All input pulses are supplied by generators having the following characteristics: PRR  $\leq 10 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r \leq 2.5 \text{ ns}$ ,  $t_f \leq 2.5 \text{ ns}$ .
  - The outputs are measured one at a time with one transition per measurement.
  - $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - $t_{PHL}$  and  $t_{PLH}$  are the same as  $t_{pd}$ .

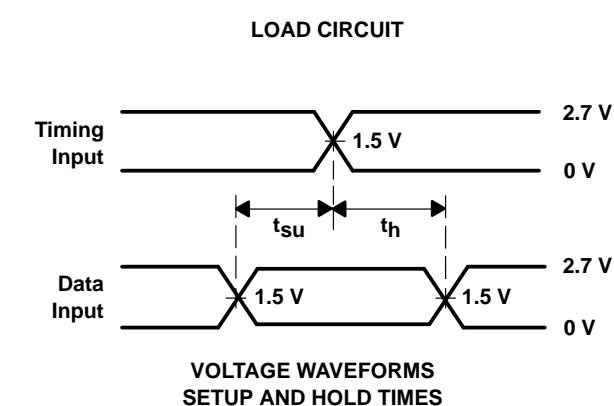
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION  
 $V_{CC} = 2.7\text{ V AND } 3.3\text{ V} \pm 0.3\text{ V}$

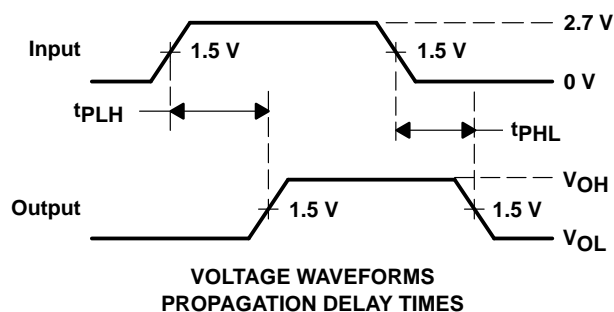


LOAD CIRCUIT

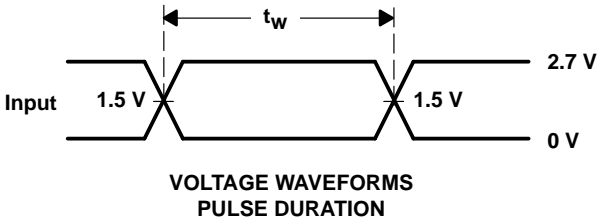
TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	6 V
$t_{PHZ}/t_{PZH}$	GND



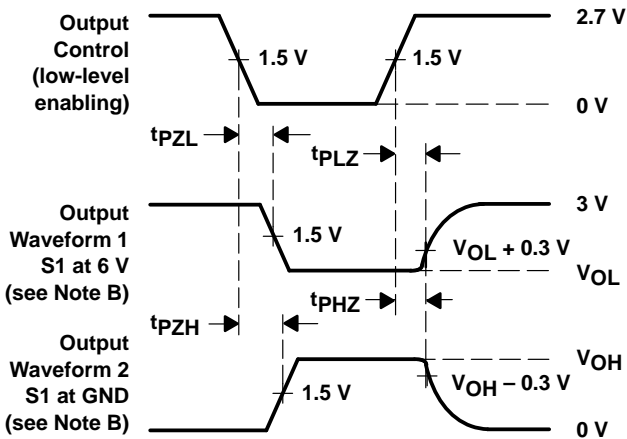
VOLTAGE WAVEFORMS  
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS  
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS  
PULSE DURATION



VOLTAGE WAVEFORMS  
ENABLE AND DISABLE TIMES

- NOTES: A.  $C_L$  includes probe and jig capacitance.  
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.  
Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.  
C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r \leq 2.5\text{ ns}$ ,  $t_f \leq 2.5\text{ ns}$ .  
D. The outputs are measured one at a time with one transition per measurement.  
E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .  
F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .  
G.  $t_{PHL}$  and  $t_{PLH}$  are the same as  $t_{pd}$ .

Figure 2. Load Circuit and Voltage Waveforms

## **IMPORTANT NOTICE**

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain applications using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

**TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.**

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.